



RELIABILITY REPORT
FOR
MAX5078BATT+
PLASTIC ENCAPSULATED DEVICES

June 15, 2010

MAXIM INTEGRATED PRODUCTS

120 SAN GABRIEL DR.
SUNNYVALE, CA 94086

Approved by
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Quality Assurance
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Conclusion

The MAX5078BATT+ successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards.

Table of Contents

I.Device Description	V.Quality Assurance Information
II.Manufacturing Information	VI.Reliability Evaluation
III.Packaging Information	IV.Die Information
.....Attachments	

I. Device Description

A. General

The MAX5078A/MAX5078B high-speed MOSFET drivers source and sink up to 4A peak current. These devices feature a fast 20ns propagation delay and 20ns rise and fall times while driving a 5000pF capacitive load. Propagation delay time is minimized and matched between the inverting and noninverting inputs. High sourcing/sinking peak currents, low propagation delay, and thermally enhanced packages make the MAX5078A/ MAX5078B ideal for high-frequency and high-power circuits. The MAX5078A/MAX5078B operate from a 4V to 15V single power supply and consume 40μA (typ) of supply current when not switching. These devices have an internal logic circuitry that prevents shoot-through during output state changes to minimize the operating current at a high switching frequency. The logic inputs are protected against voltage spikes up to +18V, regardless of the VDD voltage. The MAX5078A has CMOS input logic levels while the MAX5078B has TTL-compatible input logic levels. The MAX5078A/MAX5078B feature both inverting and noninverting inputs for greater flexibility in controlling the MOSFET. They are available in a 6-pin TDFN (3mm x 3mm) package and operate over the automotive temperature range of -40°C to +125°C.

II. Manufacturing Information

A. Description/Function:	4A, 20ns, MOSFET Driver
B. Process:	E35
C. Number of Device Transistors:	
D. Fabrication Location:	Texas
E. Assembly Location:	Thailand
F. Date of Initial Production:	July 23, 2004

III. Packaging Information

A. Package Type:	6-pin TDFN 3x3
B. Lead Frame:	Copper
C. Lead Finish:	100% matte Tin
D. Die Attach:	Conductive
E. Bondwire:	Au (1.3 mil dia.)
F. Mold Material:	Epoxy with silica filler
G. Assembly Diagram:	#05-9000-1147
H. Flammability Rating:	Class UL94-V0
I. Classification of Moisture Sensitivity per JEDEC standard J-STD-020-C	Level 1
J. Single Layer Theta Ja:	55°C/W
K. Single Layer Theta Jc:	8.5°C/W
L. Multi Layer Theta Ja:	42°C/W
M. Multi Layer Theta Jc:	8.5°C/W

IV. Die Information

A. Dimensions:	45 X 74 mils
B. Passivation:	Si ₃ N ₄ /SiO ₂ (Silicon nitride/ Silicon dioxide)
C. Interconnect:	Al/0.5%Cu with Ti/TiN Barrier
D. Backside Metallization:	None
E. Minimum Metal Width:	0.35μm
F. Minimum Metal Spacing:	0.35μm
G. Bondpad Dimensions:	5 mil. Sq.
H. Isolation Dielectric:	SiO ₂
I. Die Separation Method:	Wafer Saw

V. Quality Assurance Information

- | | |
|-----------------------------------|---|
| A. Quality Assurance Contacts: | Don Lipps (Manager, Reliability Engineering)
Bryan Preeshl (Managing Director of QA) |
| B. Outgoing Inspection Level: | 0.1% for all electrical parameters guaranteed by the Datasheet.
0.1% For all Visual Defects. |
| C. Observed Outgoing Defect Rate: | < 50 ppm |
| D. Sampling Plan: | Mil-Std-105D |

VI. Reliability Evaluation

A. Accelerated Life Test

The results of the 125°C biased (static) life test are shown in Table 1. Using these results, the Failure Rate (λ) is calculated as follows:

$$\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \times 4340 \times 93 \times 2} \quad (\text{Chi square value for MTTF upper limit})$$

(where 4340 = Temperature Acceleration factor assuming an activation energy of 0.8eV)

$$\lambda = 11.8 \times 10^{-9}$$

$$\lambda = 11.8 \text{ F.I.T. (60\% confidence level @ 25°C)}$$

The following failure rate represents data collected from Maxim's reliability monitor program. Maxim performs quarterly life test monitors on its processes. This data is published in the Reliability Report found at <http://www.maxim-ic.com/qa/reliability/monitor>. Cumulative monitor data for the E35 Process results in a FIT Rate of 0.68 @ 25C and 11.68 @ 55C (0.8 eV, 60% UCL)

B. Moisture Resistance Tests

The industry standard 85°C/85%RH or HAST testing is monitored per device process once a quarter.

C. E.S.D. and Latch-Up Testing

The NP59-6 die type has been found to have all pins able to withstand a HBM transient pulse of +/-2500V per JEDEC JESD22-A114. Latch-Up testing has shown that this device withstands a current of +/-250mA.

Table 1
Reliability Evaluation Test Results

MAX5078BATT+

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES
Static Life Test (Note 1)				
	Ta = 125°C Biased Time = 192 hrs.	DC Parameters & functionality	93	0
Moisture Testing (Note 2)				
HAST	Ta = 130°C RH = 85% Biased Time = 96hrs.	DC Parameters & functionality	77	0
Mechanical Stress (Note 2)				
Temperature Cycle	-65°C/150°C 1000 Cycles Method 1010	DC Parameters & functionality	77	0

Note 1: Life Test Data may represent plastic DIP qualification lots.

Note 2: Generic Package/Process data